Silicon NPN Power Transistors S2000A

DESCRIPTION

- With TO-3P(H)IS package
- High voltage ,high speed
- Low collector saturation voltage

APPLICATIONS

- Color TV horizontal output applications
- Color TV switching regulator applications

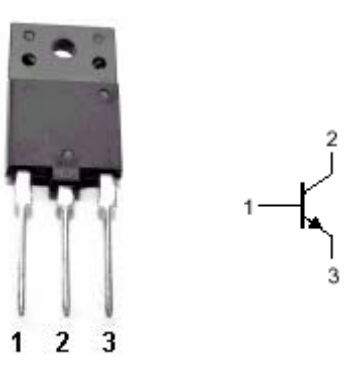


Fig.1 simplified outline (TO-3P(H)IS) and symbol

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings (T_a=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	700	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		8	A
I_{CM}	Collector current-peak		15	A
I_B	Base current		4	A
P_C	Collector power dissipation	T_C=25℃	125	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_B=500mA ;V_{BE}=-1.7V;L=40mH	700			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=1mA ;I_C=0	5			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	I_C=4.5A ;I_B=2A			1.0	V
$V_{BE(sat)}$	Base-emitter saturation voltage	I_C=4.5A ;I_B=1.0A			1.2	V
I_{CBO}	Collector cut-off current	V_{CB}=1500V; V_{BE}=0			1	mA
h_{FE-1}	DC current gain	I_C=1A ; V_{CE}=5V	10		30	
h_{FE-2}	DC current gain	I_C=4.5A ; V_{CE}=5V	4.5		9	
C_{OB}	Collector output capacitance	I_E=0 ; V_{CB}=10V;f=1MHz		95		pF
f_T	Transition frequency	I_C=0.1A ; V_{CE}=10V		2		MHz

PACKAGE OUTLINE

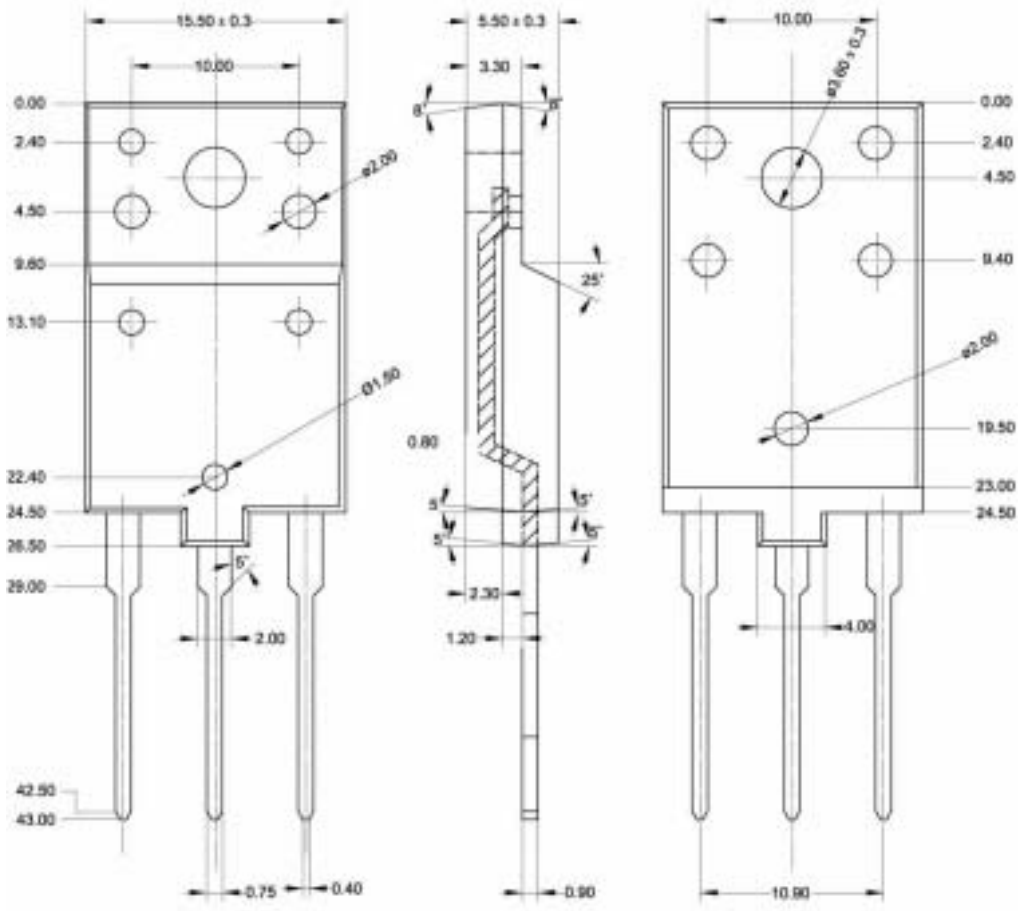


Fig.2 Outline dimensions (unindicated tolerance:±0.15 mm)

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